

IN THE SPECIFICATION:

Please replace the paragraph at page 3, line 20 - page 4, line 2 with the following amended paragraph:

This invention is characterized by including a step of selectively forming a groove or a hole by means for selectively generating plasma on a thin film having affinity for liquid, for example, silicon oxide film, silicon nitride film, silicon oxynitride film and a metal oxide film, on a substrate having insulating property, for example, a glass substrate, and discharging a drop composition onto the surface having affinity for liquid by drop discharge means, thus forming a pattern. As a groove or a hole is selectively formed on the surface having affinity for liquid, a drop can be formed without moving from its landing position after landing.